



UTG7N65-S

Insulated Gate Bipolar Transistor

650V TRENCH GATE FIELD-STOP IGBT

DESCRIPTION

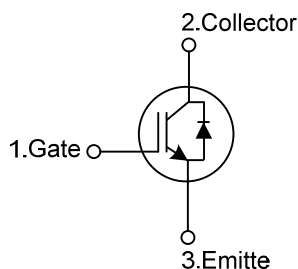
The UTC **UTG7N65-S** is an Trench Field-Stop Insulated Gate Bipolar Transistor. it uses UTC's advanced technology to provide customers with high switching speed, low saturation voltage and low switching loss, etc.

The UTC **UTG7N65-S** is suitable for the resonant or soft switching applications.

FEATURES

- * High switching speed
- * High avalanche ruggedness
- * Low saturation voltage: $V_{CE(SAT), Typ.} = 1.5V @ I_C = 7.0A, V_{GE} = 15V$ ($T_C = 25^\circ C$)

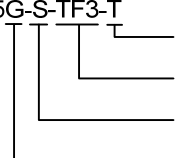
SYMBOL

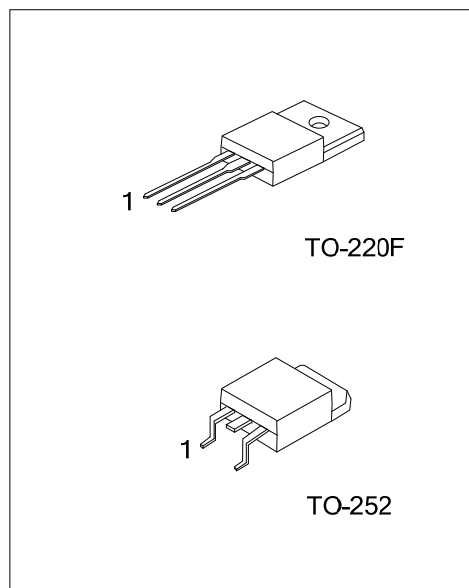


ORDERING INFORMATION

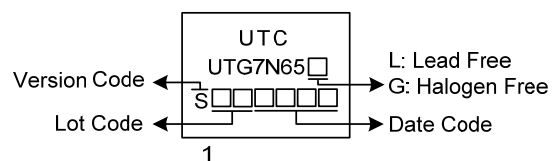
Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
UTG7N65L-S-TF3-T	UTG7N65G-S-TF3-T	TO-220F	G	C	E	Tube
UTG7N65L-S-TN3-R	UTG7N65G-S-TN3-R	TO-252	G	C	E	Tape Reel

Note: Pin Assignment: G: Gate C: Collector E: Emitter

<p>UTG7N65G-S-TF3-T</p> 		(1) Packing Type (2) Package Type (3) Version Code (4) Green Package	(1) T: Tube, R: Tape Reel (2) TF3: TO-220F, TN3: TO-252 (3) Version S (4) G: Halogen Free and Lead Free, L: Lead Free
---	--	---	--



■ MARKING



■ ABSOLUTE MAXIMUM RATINGS

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Emitter Voltage		V_{CES}	650	V
Gate-Emitter Voltage		V_{GES}	± 20	V
Transient Gate-emitter voltage ($t_p < 5\text{ ms}$)			± 25	V
Continuous Collector Current	$T_C=25^{\circ}\text{C}$	I_C	14	A
	$T_C=100^{\circ}\text{C}$		7	A
Collector Current Pulsed (Note 1)		I_{CM}	28	A
Diode Forward Current	$T_C=25^{\circ}\text{C}$	I_F	14	A
	$T_C=100^{\circ}\text{C}$		7	A
Short Circuit Withstand Time $V_{GE} = 15\text{V}$, $V_{CC} \leq 200\text{V}$ Allowed number of short circuits < 1000 Time between short circuits: $\geq 1.0\text{s}$ $T_{VJ}= 25^{\circ}\text{C}$		t_{SC}	3	μs
Power Dissipation ($T_C=25^{\circ}\text{C}$)	TO-220F	P_D	31	W
	TO-252		40	W
Operating Junction Temperature		T_J	$-40 \sim +150$	$^{\circ}\text{C}$
Storage Temperature Range		T_{STG}	$-55 \sim +150$	$^{\circ}\text{C}$

Notes: 1. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

Absolute maximum ratings are those values beyond which the device could be permanently damaged.

2. Pulse width limited by maximum junction temperature.

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Case	TO-220F	θ_{JC}	4.03	$^\circ\text{C/W}$
	TO-252		3.125 (Note)	$^\circ\text{C/W}$

Note: Device mounted on FR-4 substrate Pc board, 2oz copper, with 1inch square copper plate.

■ ELECTRICAL CHARACTERISTICS (T_C=25°C, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Off Characteristics						
Collector-Emitter Breakdown Voltage	BV _{CES}		650			V
Collector Cut-Off Current	I _{CES}	V _{CE} =650V, V _{GE} =0V			5	μA
G-E Leakage Current	I _{GES}	V _{CE} =0V, V _{GE} =±20V			±100	nA
On Characteristics						
Gate to Emitter Threshold Voltage	V _{GE(TH)}	I _C =250μA, V _{CE} =V _{GE}	4.0		6.5	V
Collector to Emitter Saturation Voltage	V _{CE(SAT)}	I _C =7.0A, V _{GE} =15V	T _C =25°C	1.5	2.1	V
			T _C =125°C	1.9		V
Dynamic Characteristics						
Input Capacitance	C _{IES}	V _{CE} =25V, V _{GE} =0V, f=1MHz		694		pF
Output Capacitance	C _{OES}			41.2		pF
Reverse Transfer Capacitance	C _{RES}			12.5		pF
Switching Characteristics						
Total Gate Charge	Q _G	V _{CE} =520V, I _C =7.0A, V _{GE} =15V		53.7		nC
Gate-Emitter Charge	Q _{GE}			15		nC
Gate-Collector Charge	Q _{GC}			23.9		nC
Turn-On Delay Time	t _{DON}	V _{CC} =650V, I _C =7.0A, R _G =5Ω, V _{GE} =0~15V, L=1000μH		16.9		ns
Rise Time	t _R			27.5		ns
Turn-Off Delay Time	t _{DOFF}			73.5		ns
Fall Time	t _F			209		ns
Turn-On Switching Loss	E _{ON}			0.254		mJ
Turn-Off Switching Loss	E _{OFF}			0.226		mJ
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Forward Voltage Drop	V _F	I _F =7.0A		1.67	3.0	V
Reverse Recovery Time	t _{rr}	I _F =7.0A, dI/dt=100A/μS,		43.3		ns
Reverse Recovery Charge	Q _{rr}	V _{CC} =400V		10.6		nC

UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. UTC reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.